

In the Specification:

Please amend the first paragraph of the specification by adding the below sentence immediately below the title thereof:

The present application is the US national stage of International Application no. PCT/EP2003/003136, filed 26 March 2003.

Please amend paragraph 3 of the application as filed, as follows:

[0003] A conventional approach of using relaxed graded SiGe layers as buffers is now described. The concept of graded SiGe buffer layers was invented in 1991 by Fitzgerald et al. The results of their work are described in F.A. Fitzgerald, Y.-H. Xie, M. L. Green, D. Brasen, A. R. Kortan, J. Michel, Y.-J Mii, and B. E. Weir, Appl. Phys. Lett., Vol. 58-59, p. 811, 1991. Such buffer layers are used as virtual substrates (VS) for applications in the area of high-speed electronics by means of metal-oxide semiconductor field-effect transistors (MOSFETs) and modulation-doped field-effect transistors (MODFETs) based on strained Si or $\text{Si}_{1-x}\text{Ge}_x$ ($0 < x \leq 1$). The active layers (e.g., Si) on top of a VS are strained because the VS has a lattice parameter intermediate between that of Si and Ge.